



Junction Evaluation using Electron Beam Induced Current (EBIC)

Gary Mount Mike Salmon

Copyright © 2013 Evans Analytical Group



- EBIC only works if there is an electrical junction.
- An electron beam is injected into a sample, electron-hole pairs are formed, but they are only separated causing current to flow in the presence of an electric field, such as that caused by a p-n junction.
- The strength of the signal depends on the quality of the junction.
- EBIC can be done using a standard SEM or with considerable effort, in a TEM.



- EBIC is a useful tool for the evaluation of electrical junction performance uniformity.
- EBIC is a useful tool for finding the location of an electrical junction.
- It is very useful for large area junctions such as:
 LED
 - Solar Cells
- EBIC combined with other analytical tools can find layer and crystal structure defects.

p-n Junction Fundamentals

Evans Analytical Group





- Electron-Hole pair generation
- Can be generated by a photon (OBIC)
- Can be generated by an electron (EBIC)





- Layer structure and crystal structure defect evaluation is traditionally done by random selection.
- EBIC provides information on where to look.

Example: Commercial GaN LED





AG Rapid Typing of Dislocations



- The character of dislocations can be quickly determined using STEM imaging.
- By utilizing specific sample tilts, threading dislocations can be identified as having screw, edge, or mixed character.

E-beam Interaction with a Surface





• Plan-View



- Current flows when SEM electron beam penetrates p-n junction.
- Uniformity of current flow depends on uniformity of electrical junction.
- Contrast created by non-uniformities in junction.

G Finding Defects using EBIC



- Electron Beam Induced Current (EBIC) imaging is compared with standard SEM imaging. An EBIC 'bright spot' reveals a defect that is not seen in standard SEM.
- The contrast at the Defect is caused by current changes in the p-n junction. Why?

EAG Analysis of EBIC Discovered Defect



- Same defect as previous slide.
- Cross section prepared.
- Large EBIC bright spot correlates with quantum well structure.
- Small EBIC bright spot correlates with pit defect.





EBIC in the **TEM**

Copyright © 2013 Evans Analytical Group



- Resolution in standard EBIC is limited by the electron beam interaction volume.
- EBIC in the STEM has the promise of much higher resolution.



Compare STEM and TEM







Z-Contrast Image of QW Structure



Z-contrast image, showing the GaN and AlGaN barrier layers and the InGaN quantum well. STEM has unique capabilities in providing Z-contrast images.



Cross-Section



- EBIC imaging can be done on a thin cross-section prepared for STEM
- The electron beam scanned over a cross-section reveals the location of the p-n junction within the quantum well.



EBIC current only flows when the electron beam hits the p-n junction







CIGS Layer Structure



- TCO layers show columnar ITO grains, a very thin (15nm) ZnO layer, and CdS with no apparent grain structure.
- The layers appear conformal with the CIGS surface and have good layer uniformity.
- The 15nm ZnO layer cannot be seen by any other method.







EXAMPLE A STEM and EBIC Images



EBIC Signal

Permission not granted to show data





Permission not granted to show data



- Sample type determines analysis
 - Plan-view (SEM)
 - Cross-section (STEM)
- Plan view EBIC can find defects under the surface.
- Cross-section EBIC shows junction location.
- STEM can greatly improve resolution limits.





www.eaglabs.com